

# 2SC495 2SC496

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

MEDIUM POWER AMPLIFIER APPLICATIONS.

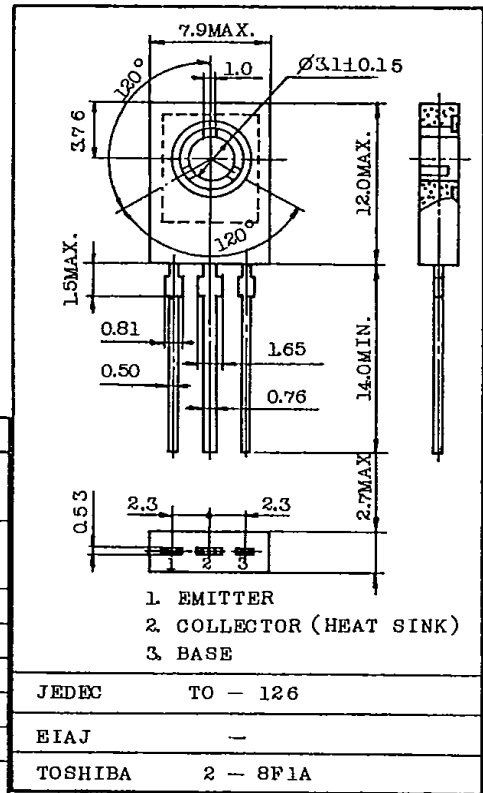
FEATURES:

- Low Collector Saturation Voltage  
:  $V_{CE(sat)}=0.25V$  (Typ.)
- 0.5 ~ 2 Watts Output Application.
- Complementary to 2SA505 and 2SA496.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	2SC495	70
		2SC496	40
Collector-Emitter Voltage	V <sub>CEO</sub>	2SC495	50
		2SC496	30
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>C</sub>	1	A
Emitter Current	I <sub>E</sub>	-1	A
Collector Power Dissipation	P <sub>C</sub>	1	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 ~ 150	°C

Unit in mm



Mounting Kit No. AC46C  
Weight : 0.72g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> =30V, I <sub>E</sub> =0	-	-	1.0	µA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0	-	-	1.0	µA
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	2SC495	50	-	-
			2SC496	30	-	-
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =1mA, I <sub>C</sub> =0	5	-	-	V
DC Current Gain	h <sub>FE(1)</sub> (Note)	V <sub>CE</sub> =2V, I <sub>C</sub> =50mA	40	-	240	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =800mA	13	-	-	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	-	0.25	0.8	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =500mA	-	0.9	1.1	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	50	100	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz	-	10	-	pF

Note : h<sub>FE(1)</sub> Classification R : 40~80, O : 70~140, Y : 120~240

